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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/727,387	12/04/2003	Kevin L. Robinson	LMC-34	7745
7590 11/09/2005			EXAMINER	
PLEVY & HOWARD 600 NORTH EASTON ROAD WILLOW GROVE, PA 19090			LUU, CHUONG A	
			ART UNIT	PAPER NUMBER
			2818	

DATE MAILED: 11/09/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/727,387

Applicant(s)

ROBINSON, KEVIN L.

Examiner

Chuong A. Luu

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 03 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 19 August 2005.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-19 is/are pending in the application.
- 4a) Of the above claim(s) 1 and 2 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 3-19 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date 8/19/2005.
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

DETAILED ACTION

Response to Arguments

Applicant's arguments with respect to claims 3-19 have been considered but are moot in view of the new ground(s) of rejection.

PRIOR ART REJECTIONS

Statutory Basis

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

The Rejections

Claims 3-19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Song (U.S. 20020177261 A1) in view of Kim et al. (U.S. 6,593,603 B1).

Song discloses an integrated circuit device with

(3); (10) a first block comprising an enhancement mode PHEMT transistor on a substrate;

a second block comprising a depletion mode PHEMT transistor on the substrate, the second block operatively connected to the first block (see paragraphs [0024]-[0031]. Figure 4);

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(4) further comprising: b: a clock input in communication with at least one of the first block, the second block;

c: a digital output in communication with at least one of the first block, the second block;

d: wherein the first block, the second block connect to form an analog to digital converter (see paragraphs [0024]-[0031]. Figure 4);

(5) wherein the integrated circuit is a microwave and millimeter wave integrated circuit (MMIC) (see paragraph [0003]);

(6) wherein the circuit is a circuit capable of operating at a frequency within the range of from very low frequency up to and including X-band frequencies (see paragraph [0002]);

(8) wherein the substrate comprises a group III-V element (see paragraph [0013]);

(9) wherein the substrate comprises gallium arsenide (see paragraph [0013]);

(11) wherein the plurality of integrated circuits can be interconnected to form a plurality of functional blocks which can be interconnected to create an operational electronic device (see Figure 4);

(12) wherein each of said PHEMT transistors comprises a recess defined in said substrate and a gate formed in said recess (see Figure 4);

(13) wherein the recess of the depletion mode PHEMT transistor is a single recess (see Figure 4);

(15) wherein the recess of the enhancement mode PHEMT transistor is a single recess (see Figure 4);

(16) wherein the recess of the depletion mode PHEMT transistor is a single recess, and each of said recesses is defined through at least one common layer of said substrate (see Figure 4).

Song teaches the above outlined features except for a third block comprising a power PHEMT transistor on the substrate, the third block operatively connected to at least one of the first block and the second block; wherein the recess of the power PHEMT transistor is a double recess; wherein the recess of the power PHEMT transistor is a double recess; wherein at least one of said gates is a T-gate; wherein a pinch off voltage of the depletion-mode PHEMT transistor is about positive 0.1 volts; and wherein a pinch off voltage of the enhancement-mode PHEMT transistor is about negative 1.0 volts. However, Kim discloses a high electron mobility transistor with **(3)**; **(4)**; **(7)**... a third block comprising a power PHEMT transistor on the substrate, the third block operatively connected to at least one of the first block and the second block; an analog input in communication with at least one of the first block, the second block (see column 2, lines 7-45. Figure 1); **(7)** an analog to digital converter, comprising an enhancement mode PHEMT device, a depletion mode PHEMT device on a single substrate (see column 1, lines 15-35. Figure 1); **(14)**; **(16)** wherein the recess of the power PHEMT transistor is a double recess; **(17)** wherein at least one of said gates is a T-gate (see Figure 1); **(18)** wherein a pinch off voltage of the depletion-mode PHEMT transistor is about positive 0.1 volts (see column 5, lines 45-61); **(19)** wherein a pinch

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off voltage of the enhancement-mode PHEMT transistor is about negative 1.0 volts (see column 5, lines 45-61). Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the Song's device (accordance with the teaching of Kim) to form a transistor since it has been held that mere duplication of the essential working parts of a device involves only routine skill in the art. *St. Regis Paper Co. v. Bemis Co.*, 193 USPQ 8. Doing so would facilitate the manufacture of the semiconductor device and improve the speed of the semiconductor transistor.

Response to Arguments

Applicant's arguments with respect to claims 3-19 have been considered but are moot in view of the new ground(s) of rejection.

Applicant argues that Taylor fails to teach or suggest all of the limitations of the rejected claims. However, Song discloses an integrated circuit device comprising an enhancement mode PHEMT transistor on a substrate; a second block comprising a depletion mode PHEMT transistor on the substrate, the second block operatively connected to the first block (see paragraphs [0024]-[0031]. Figure 4). In addition, Kim discloses a high electron mobility transistor with **(3); (4); (7)**... a third block comprising a power PHEMT transistor on the substrate, the third block operatively connected to at least one of the first block and the second block (see column 2, lines 7-45. Figure 1). Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the Song's device (accordance with the teaching of

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Kim) to form a transistor since it has been held that mere duplication of the essential working parts of a device involves only routine skill in the art. *St. Regis Paper Co. v. Bemis Co.*, 193 USPQ 8. Doing so would facilitate the manufacture of the semiconductor device and improve the speed of the semiconductor transistor.

Conclusion

Applicant's submission of an information disclosure statement under 37 CFR 1.97(c) with the fee set forth in 37 CFR 1.17(p) on *** prompted the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 609.04(b). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire **THREE MONTHS** from the mailing date of this action. In the event a first reply is filed within **TWO MONTHS** of the mailing date of this final action and the advisory action is not mailed until after the end of the **THREE-MONTH** shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than **SIX MONTHS** from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Chuong A. Luu whose telephone number is (571) 272-1902. The examiner can normally be reached on M-F (6:15-2:45).

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David C. Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

A handwritten signature in black ink, appearing to read 'Chuong Anh Luu', is positioned above the printed name and title.

Chuong Anh Luu
Patent Examiner
October 24, 2005